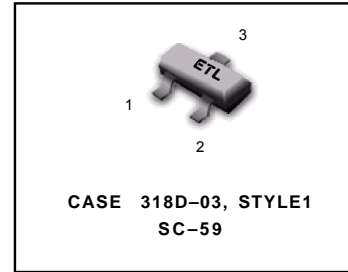
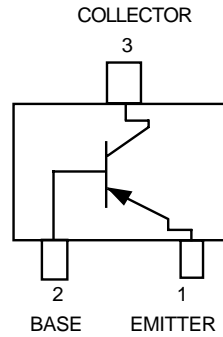


PNP RF Amplifier Transistor

Surface Mount

MSA1022-CT1



MAXIMUM RATINGS (T_A = 25 °C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-30	Vdc
Collector-Emitter Voltage	V _{CEO}	-20	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-30	mAdc

THERMAL CHARACTERISTICS

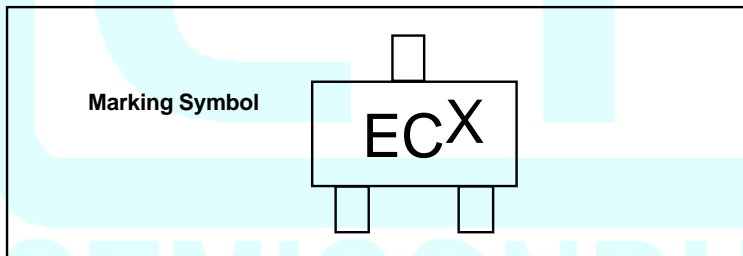
Characteristic	Symbol	Max	Unit
Power Dissipation	P _D	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Characteristic	Symbo	IMin	Max	Unit
Collector Cutoff Current (V _{CB} = -10 Vdc, I _E = 0)	I _{CB0}	—	-0.1	μAdc
Collector-Emitter Breakdown Voltage (V _{CE} = -20 Vdc, I _B = 0)	I _{CEO}	—	-100	μAdc
Emitter-Base Breakdown Voltage (V _{EB} = -5.0 Vdc, I _C = 0)	I _{EBO}	—	-10	μAdc
DC Current Gain (1) (V _{CE} = -10 Vdc, I _C = -1.0 mAdc)	h _{FE}	110	220	—
Current-Gain - Bandwidth Product (V _{CB} = -10 Vdc, I _E = 1.0 mAdc)	f _T	150	—	MHz

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.